## **Atabek Atamuratov**

List of Publications by Year in descending order

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2258059 1720034 10 48 3 7 citations h-index g-index papers 10 10 10 69 citing authors docs citations times ranked all docs

#	Article	IF	CITATIONS
1	Amplitude of Random Telegraph Noise in Junctionless FinFET with Different Channel Shape. E-Journal of Surface Science and Nanotechnology, 2021, 19, 9-12.	0.4	O
2	The Self-Heating Effect in Junctionless Fin Field-Effect Transistors Based on Silicon-on-Insulator Structures with Different Channel Shapes. Technical Physics Letters, 2021, 47, 542-545.	0.7	1
3	Contribution to the Physical Modelling of Single Charged Defects Causing the Random Telegraph Noise in Junctionless FinFET. Applied Sciences (Switzerland), 2020, 10, 5327.	2.5	O
4	Lateral Capacitance–Voltage Method of NanoMOSFET for Detecting the Hot Carrier Injection. Applied Sciences (Switzerland), 2020, 10, 7935.	2.5	3
5	The Effect of the Fin Shape and Thickness of the Buried Oxide on the DIBL Effect in an SOI FinFET. Technical Physics Letters, 2018, 44, 962-964.	0.7	4
6	Influence of the field of the built-in oxide charge on the lateral C-V dependence of the MOSFET. Doklady Physics, 2010, 55, 52-54.	0.7	2
7	Photoassisted Kelvin probe force microscopy at GaN surfaces: The role of polarity. Applied Physics Letters, 2010, 97, .	3.3	31
8	Tunable SiO2/Si-based nanostructures. Inorganic Materials, 2009, 45, 900-904.	0.8	0
9	Detection of a charge built in the oxide layer of a metal-oxide-semiconductor field-effect transistor by lateral C-V measurement. Doklady Physics, 2007, 52, 322-325.	0.7	3
10	Title is missing!. Inorganic Materials, 2001, 37, 767-768.	0.8	4